

Vishay General Semiconductor

Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.47 \text{ V}$ at $I_F = 10 \text{ A}$



| PRIMARY CHARACTERISTICS | | | | |
|-------------------------------|---------------------|--|--|--|
| I _{F(AV)} | 2 x 30 A | | | |
| V_{RRM} | 100 V | | | |
| I _{FSM} | 350 A | | | |
| E _{AS} at L = 180 mH | 700 mJ | | | |
| V_F at $I_F = 30 A$ | 0.66 V | | | |
| T _J max. | 150 °C | | | |
| Package | TO-3PW | | | |
| Diode variations | Dual common cathode | | | |

FEATURES

- Trench MOS Schottky technology
- · Low forward voltage drop, low power losses

High efficiency operation

ROHS COMPLIANT HALOGEN

- Solder dip 275 °C max. 10 s, per JESD 22-B106
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

MECHANICAL DATA

Case: TO-3PW

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant, and

commercial grade

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

| PARAMETER | SYMBOL | V60100PW | UNIT | | | |
|---|-----------------|-----------------------------------|-------------|------------------|-----|---|
| FANAIVIETEN | | STWIDOL | V00100FVV | ONIT | | |
| Maximum repetitive peak reverse voltage | | V_{RRM} | 100 | V | | |
| Maximum average forward rectified current (fig. 1) | per device | | 60 | ^ | | |
| | per diode | I _{F(AV)} | 30 | A | | |
| Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode | | I _{FSM} | 350 | А | | |
| Non-repetitive avalanche energy at $T_J = 25$ °C, $L = 180$ I | E _{AS} | 700 | mJ | | | |
| Peak repetitive reverse current at t_p = 2 μ s, 1 kHz, T_J = 38 °C \pm 2 °C per diode | | | | I _{RRM} | 1.0 | А |
| Voltage rate of change (rated V _R) | | dV/dt | 10 000 | V/µs | | |
| Operating junction and storage temperature range | | T _J , T _{STG} | -40 to +150 | °C | | |



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| ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted) | | | | | | |
|---|-------------------------|-------------------------|-------------------------------|---------------|------|------|
| PARAMETER | TEST CONDITIONS | | SYMBOL | TYP. | MAX. | UNIT |
| Breakdown voltage | I _R = 1.0 mA | T _A = 25 °C | V_{BR} | 100 (minimum) | - | V |
| Instantaneous forward voltage per diode | I _F = 10 A | T _A = 25 °C | V _F ⁽¹⁾ | 0.52 | - | . v |
| | I _F = 15 A | | | 0.58 | - | |
| | I _F = 30 A | | | 0.75 | 0.86 | |
| | I _F = 10 A | T _J = 125 °C | | 0.47 | - | |
| | I _F = 15 A | | | 0.54 | - | |
| | I _F = 30 A | | | 0.66 | 0.74 | |
| Reverse current per diode | V _R = 80 V | T _A = 25 °C | I _R ⁽²⁾ | 35 | - | μΑ |
| | | T _A = 125 °C | | 10 | - | mA |
| | V _R = 100 V | T _A = 25 °C | | - | 1000 | μΑ |
| | | T _A = 125 °C | | 19 | 66 | mA |

Notes

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

| THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted) | | | | | | |
|---|------------|---------------|----------|--------|--|--|
| PARAMETER | | SYMBOL | V60100PW | UNIT | | |
| Typical thermal resistance | per diode | $R_{	hetaJC}$ | 1.5 | - °C/W | | |
| | per device | | 0.8 | | | |

| ORDERING INFORMATION (Example) | | | | | | | |
|--------------------------------|----------------|-----------------|--------------|---------------|---------------|--|--|
| PACKAGE | PREFERRED P/N | UNIT WEIGHT (g) | PACKAGE CODE | BASE QUANTITY | DELIVERY MODE | | |
| TO-3PW | V60100PW-M3/4W | 4.5 | 4W | 30/tube | Tube | | |

RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

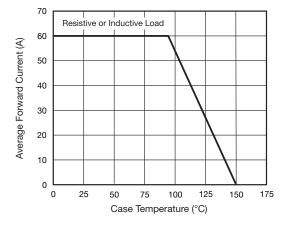


Fig. 1 - Forward Current Derating Curve

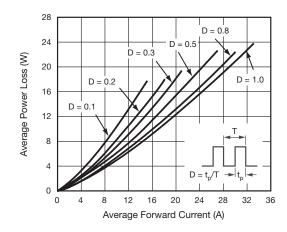


Fig. 2 - Forward Power Loss Characteristics Per Diode



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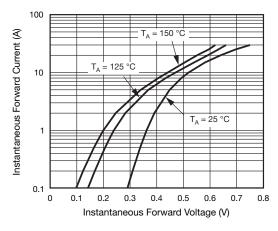


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

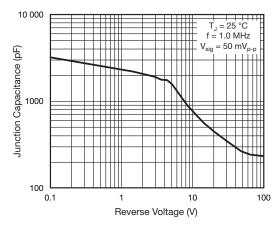


Fig. 5 - Typical Junction Capacitance Per Diode

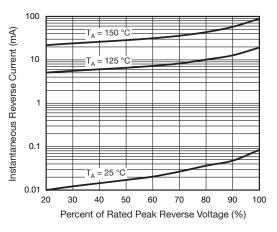


Fig. 4 - Typical Reverse Characteristics Per Diode

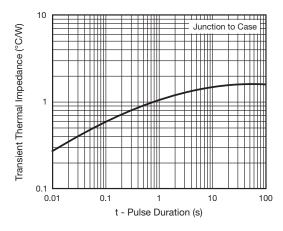
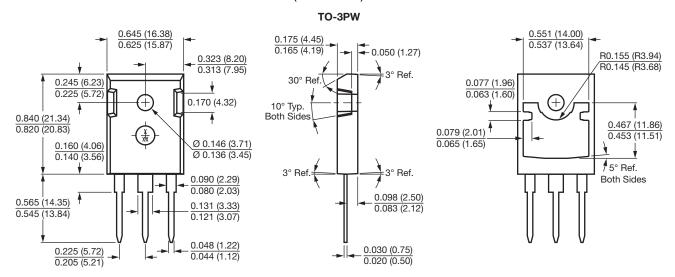


Fig. 6 - Typical Transient Thermal Impedance Per Diode

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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